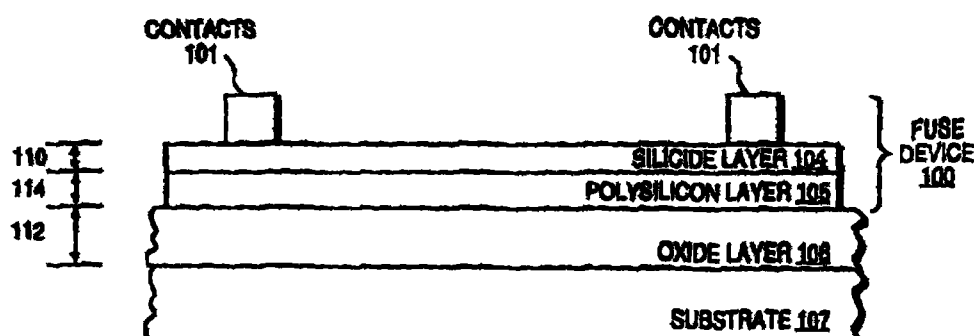


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(54) Title: A SILICIDE AGGLOMERATION FUSE DEVICE**(57) Abstract**

A fusible link device (100) disposed on a semiconductor substrate (107) for providing discretionary electrical connections. The fusible link device of the invention includes a silicide layer (104) and a polysilicon layer (105), with the silicide layer formed on the polysilicon layer, and has a first unprogrammed resistance. The silicide layer agglomerates to form an electrical discontinuity in response to a predetermined programming potential being applied across the silicide layer, such that the resistance of the fusible link device can be selectively increased to a second programmed resistance.